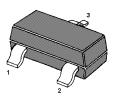
MMBTSA1576

PNP Silicon Epitaxial Planar Transistor

The transistor is subdivided into three groups Q, R and S according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1.BASE 2.EMITTER 3.COLLECTOR TO-236 Plastic Package

Features

• Excellent h_{FE} linearity

Absolute Maximum Ratings (T_a = 25 °C)

	Symbol	Value	Unit
Collector Base Voltage	-V _{CBO}	60	V
Collector Emitter Voltage	-V _{CEO}	50	V
Emitter Base Voltage	-V _{EBO}	6	V
Collector Current	-I _C	150	mA
Power Dissipation	P _{tot}	200	mW
Junction Temperature	Tj	150	°C
Storage Temperature Range	T _{Stg}	-55 to +150	°C



Characteristics at T_{amb}=25 °C

		Symbol	Min.	Тур.	Max.	Unit
DC Current Gain						
at $-V_{CE} = 6V$, $-I_{C} = 1$ mA	Q	h _{FE}	120	-	270	-
	R	h _{FE}	180	-	390	-
	S	h _{FE}	270	-	560	-
Collector Cutoff Current at $-V_{CB} = 60 \text{ V}$		-I _{CBO}	-	-	0.1	μA
Emitter Cutoff Current at -V _{EB} = 6 V		-I _{EBO}	-	-	0.1	μA
Collector Saturation Voltage at $-I_C = 50$ mA, $-I_B = 5$ mA		-V _{CE(sat)}	-	-	0.5	V
Collector Base Breakdown Voltage at $-I_C = 50 \ \mu A$		-V _{(BR)CBO}	60	-	-	V
Collector Emitter Breakdown Voltage at -I _C = 1 mA		-V _{(BR)CEO}	50	-	-	V
Emitter Base Breakdown Voltage at -I _E = 50 µA		-V _{(BR)EBO}	6	-	-	V
Transition Frequency at $-V_{CE} = 12 \text{ V}, -I_E = 2 \text{ mA}, f = 30 \text{ MHz}$		f⊤	-	140	-	MHz
Output Capacitance at $-V_{CB}$ = 12 V, f = 1 MHz		Cob	-	-	5	pF



